



Form PTO-1449		 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1670	SERIAL NO. 09/881,407			
LIST OF ART CITED BY APPLICANT <small>(See 37 CFR 1.56(c) sheets if necessary)</small>				APPLICANT Zhongze Wang				
				FILING DATE June 13, 2001	GROUP 2811			
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
PEP	AA	5,254,489	10/19/93	Nakata				
PEP	AB	5,464,792	11/07/95	Tseng et al.				
PEP	AC	5,596,218	01/21/97	Soleimani et al.				
PEP	AD	5,620,908	04/15/97	Inoh et al.				
PEP	AE	5,674,788	10/07/97	Wristers et al.				
PEP	AF	5,716,864	02/10/98	Abe				
PEP	AG	5,960,302	09/28/99	Ma et al.				
PEP	AH	5,972,783	10/26/99	Arai et al.				
PEP	AI	5,994,749	11/30/99	Oda				
PEP	AJ	6,225,151	05/01/01	Gardner et al.				
PEP	AK	4,651,406	03/24/87	Shimizu et al.				
FOREIGN PATENT DOCUMENTS						RECEIVED OCT 13 2001 TECHNOLOGY CENTER		
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
PEP	AL	WO 96/39713	12/12/96	PCT				
PEP	AM	JP06302813A	04/09/93	Japan (Citizen Watch Co. Ltd.)				
	AN							
	AO							
	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
PEP	AR		Doyle et al., "Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing", IEEE Electron Device Letters, Vol. 16, No. 7.					
PEP	AS		Ko et al., "The Effect of Nitrogen Incorporation Into the Gate Oxide by Using Shallow Implantation of Nitrogen and Drive-in Process", 1998 IEEE, 0-7803-4932-6/98.					
	AT		Kurni et al., "The Effects of Nitrogen Implantation Into P+ Poly-Silicon Gate on Gate Oxide Properties", 1994 Symposium on VLSI Technology Digest of Technical Papers, pp. 107-108.					
EXAMINER <i>Anita R. Patis</i>				DATE CONSIDERED <i>17 Sept. 2002</i>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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<div style="display: flex; align-items: center;"> <div style="border: 1px solid black; border-radius: 50%; padding: 10px; text-align: center; margin-right: 10px;"> OIP OCT 15 2001 PATENT & TRADEMARK OFFICE </div> <div> LIST OF ART CITED BY APPLICANT (Use several sheets if necessary) </div> </div>				APPLICANT Zhongze Wang			
FILING DATE June 13, 2001				GROUP 2811			
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
REP	AA	5,502,009	03/26/96	Lin			
REP	AB	6,136,654	10/24/00	Kraft et al.			
REP	AC	6,165,846	12/26/00	Carns et al.			
REP	AD	6,200,834-B1	03/13/01	Bronner et al.			
REP	AE	6,093,661	07/25/00	Trivedi et al.			
	AF						
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	AH						
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	AK						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AL						
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	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
REP	AR		C.T. Liu et al.; "Multiple Gate Oxide Thickness for 2GHz System-on-a-Chip Technologies"; IEEE 1998; pp. 21.2.1-21.2.4				
	AS						
	AT						
EXAMINER			DATE CONSIDERED				
			17 Sept. 2002				
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
REP	AA	5,763,922	06/09/98	Chau				
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
	AL							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
REP	AM	326352	11/01	Japan				
	AN							
	AO							
	AP							
	AQ							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AR							
	AS							
	AT							
EXAMINER <i>Paula E. Perkins</i>				DATE CONSIDERED 17 Sept. 2002				
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